PMZ600UNE

20 V, N-channel Trench MOSFET

26 June 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 470 m Ω

3. Applications

- · Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	0.6	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 0.6 A; T_j = 25 °C		-	470	620	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZ600UNE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ600UNE	SA

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	0.6	Α
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	0.4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	2.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
Is	source current	T _{amb} = 25 °C	[1]	-	0.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

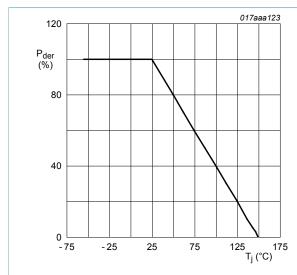


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

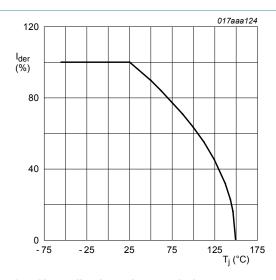


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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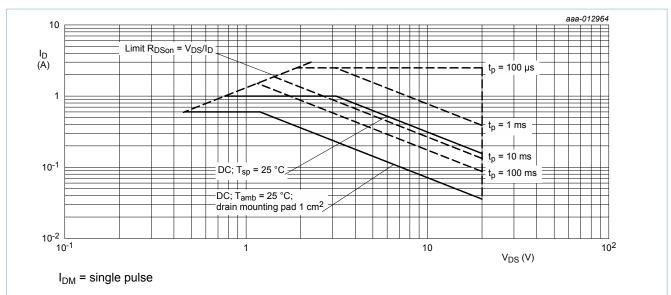


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	305	360	K/W
	from junction to ambient	-	[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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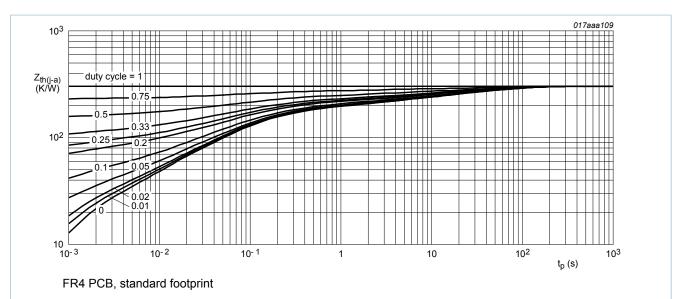


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

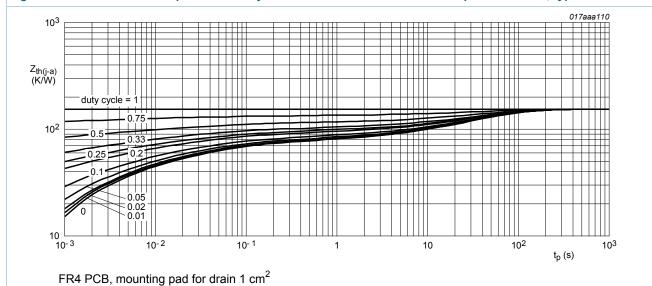


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					_
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	0.95	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 0.6 A; T _j = 25 °C	-	470	620	mΩ
resis	resistance	V _{GS} = 4.5 V; I _D = 0.6 A; T _j = 150 °C	-	760	1000	mΩ
		V _{GS} = 2.5 V; I _D = 0.5 A; T _j = 25 °C	-	620	850	mΩ
		V _{GS} = 1.8 V; I _D = 0.1 A; T _j = 25 °C	-	845	1300	mΩ
		V _{GS} = 1.5 V; I _D = 10 mA; T _j = 25 °C	-	1125	3000	mΩ
		V _{GS} = 1.2 V; I _D = 1 mA; T _j = 25 °C	-	2210	-	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 0.6 \text{ A}; T_j = 25 \text{ °C}$	-	1	-	S
R _G	gate resistance	f = 1 MHz	-	34	-	Ω
Dynamic c	haracteristics			-		
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 0.6 A; V_{GS} = 4.5 V;	-	0.4	0.7	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	21.3	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$	-	5.4	-	pF
C _{rss}	reverse transfer capacitance		-	4.2	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I_{D} = 0.6 A; V_{GS} = 4.5 V;	-	5.6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	9.2	-	ns
t _{d(off)}	turn-off delay time		-	19	-	ns
t _f	fall time		-	51	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 0.36 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	0.8	1.2	V

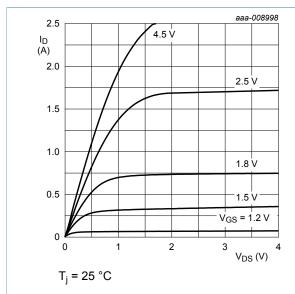


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

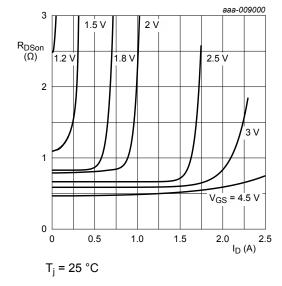


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

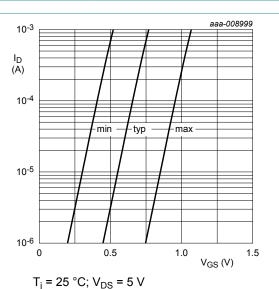


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

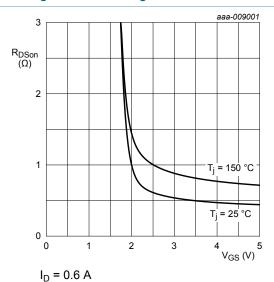


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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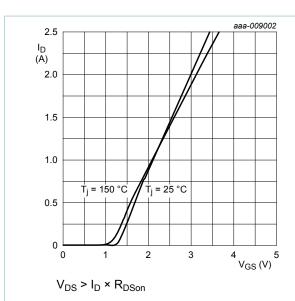


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

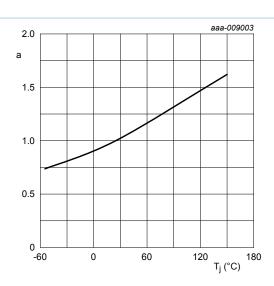


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

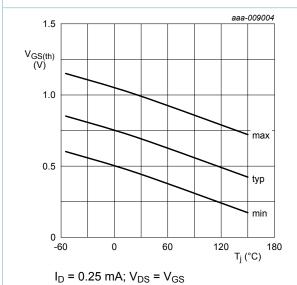
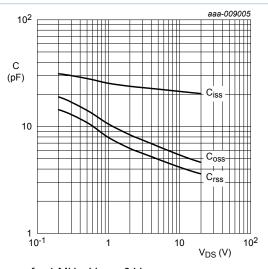


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

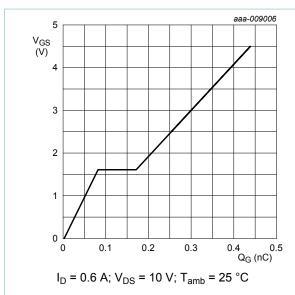
Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

V_{DS} _

 $V_{GS(pl)}$

 $V_{GS(th)}$ V_{GS}

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Q_{G(tot)} 017aaa137

Fig. 15. MOSFET transistor: Gate charge waveform definitions

Q_{GS2}

-Q_{GD}-

Q_{GS1}

Fig. 14. Gate-source voltage as a function of gate charge; typical values

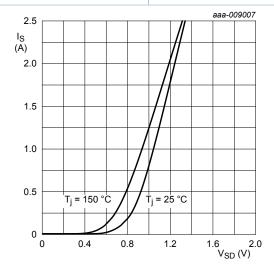
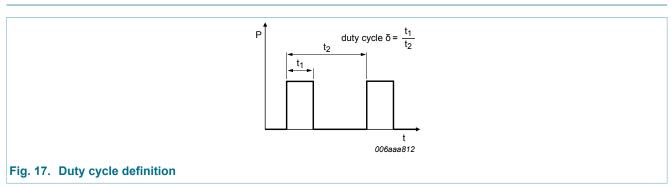


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

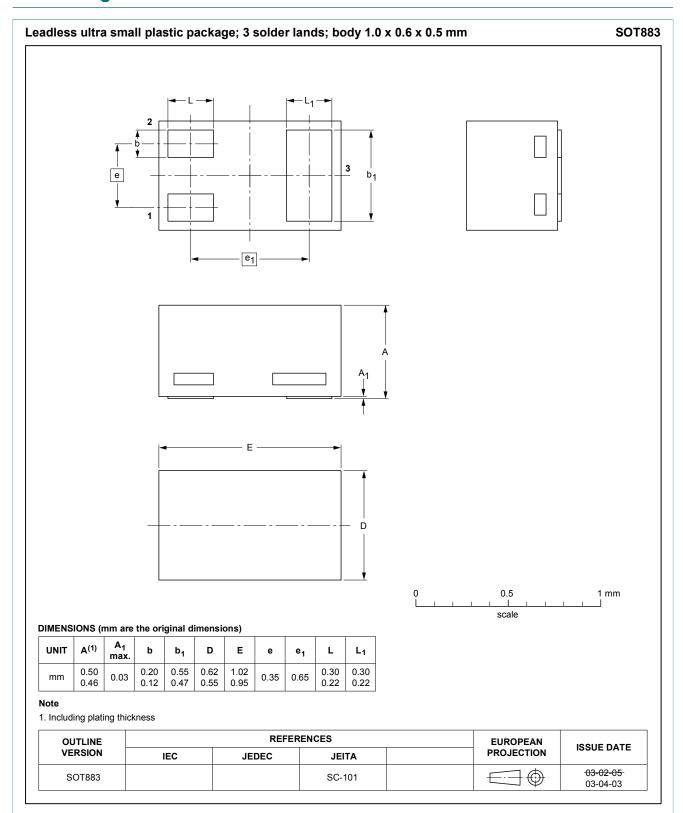
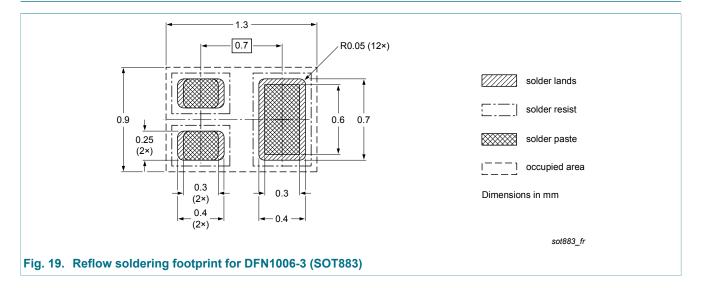


Fig. 18. Package outline DFN1006-3 (SOT883)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMZ600UNE v.2	20140626	Product data sheet	Product data sheet	PMZ600UNE v.1	
Modifications:	Limiting values parameter source current corrected.				
PMZ600UNE v.1	20140509	Product data sheet	-	-	

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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